



2813
11/3/02
PATENT
740756-2222

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT application of:)
Shunpei YAMAZAKI et al.) Art Unit: 2813
Application No.: 09/699,466) Examiner: T. NGUYEN
Filed: October 31, 2000)
For: METHOD FOR FABRICATING A)
SEMICONDUCTOR DEVICE)

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DEC 31 2001

TC 2800, MAIL ROOM

December 26, 2001

AMENDMENT

Commissioner of Patents
Washington, D.C. 20231

Dear Sir:

In response to the Examiner's non-Final Office Action mailed September 26, 2001, please consider the following amendments and remarks in connection with the above-identified application.

IN THE CLAIMS:

Please add the following new claims 26-34 as follows:

--26 A method for manufacturing a thin film transistor, comprising the steps of:

forming a semiconductor film on an insulating surface;

crystallizing said semiconductor film;

forming a semiconductor island having a tapered shape by patterning said semiconductor film, said tapered shape having an angle within a range of 20° to 50° between a side thereof and an underlying surface;

irradiating laser light to said semiconductor island; and

forming an insulating film on said semiconductor island.

12/27/2001 MGE BREM1 00000035 09699466

01 FC:102
02 FC:103
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